

ROITHNER LASERTECHNIK

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RLT67100G TECHNICAL DATA



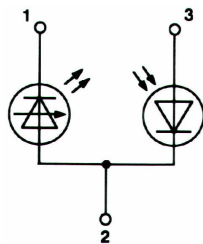
High Power Visible Wavelength Laserdiode

Structure: InGaAlP/GaAs, Aperture: 1 x 30 μm
 Lasing wavelength: 675 nm, multimode
 Max. optical power: 110 mW
 Package: 9 mm

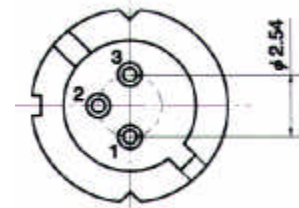
NOTE!
 LASERDIODE
 MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	110	mW
LD Reverse Voltage	$V_{R(LD)}$	0.5	V
PD Reverse Voltage	$V_{R(PD)}$	5	V
Operation Case Temperature	T_C	-20 .. +40	°C
Storage Temperature	T_{STG}	-60 .. +70	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		100		mW
Threshold Current	I_{th}	cw	100	110	130	mA
Operation Current	I_{op}	$P_o = 100 \text{ mW}$		230	250	mA
Operating Voltage	V_{op}	$P_o = 100 \text{ mW}$		2.3	2.4	V
Lasing Wavelength	λ_p	$P_o = 100 \text{ mW}$	660	675	695	nm
Beam Divergence	$\theta_{//}$	$P_o = 100 \text{ mW}$	6	10	16	°
Beam Divergence	θ_{\perp}	$P_o = 100 \text{ mW}$		30		°
Monitor Current	I_m	$P_o = 100 \text{ mW}$	300	400	600	μA